

2SC1847

Silicon NPN epitaxial planar type

For medium output power amplification

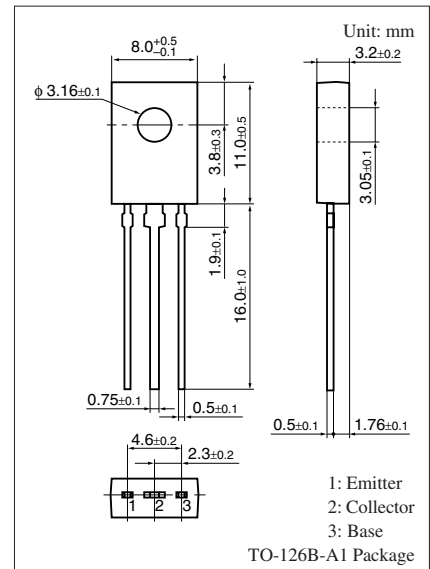
Complementary to 2SA0886

■ Features

- Output of 4 W can be obtained by a complementary pair with 2SA0886
- TO-126B package which requires no insulation plate for installation to the heat sink

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|------------------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 50 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 40 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 5 | V |
| Collector current | I_{C} | 1.5 | A |
| Peak collector current | I_{CP} | 3 | A |
| Collector power dissipation | P_{C} | 1.2 | W |
| Junction temperature | T_{j} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |



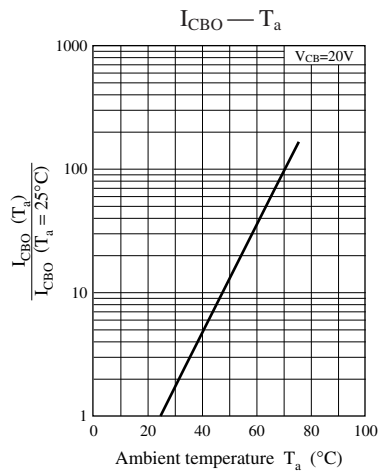
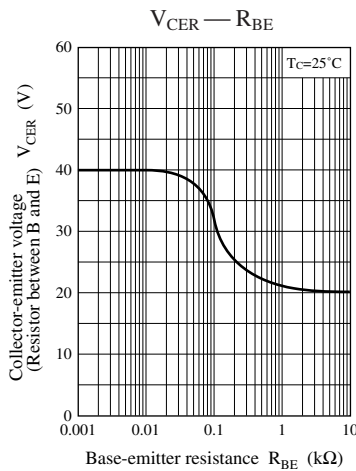
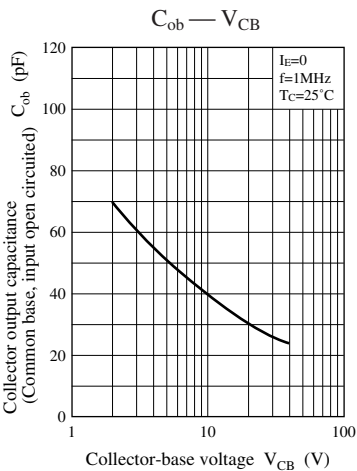
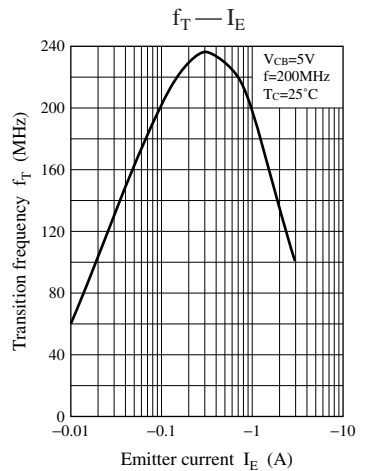
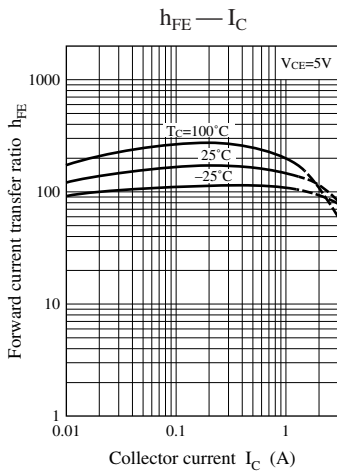
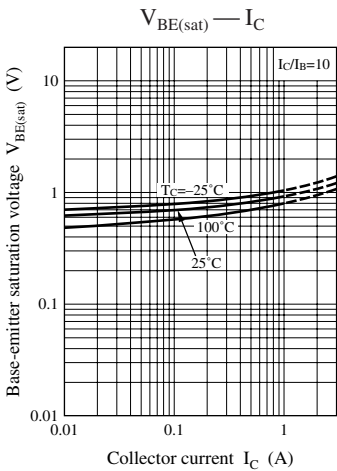
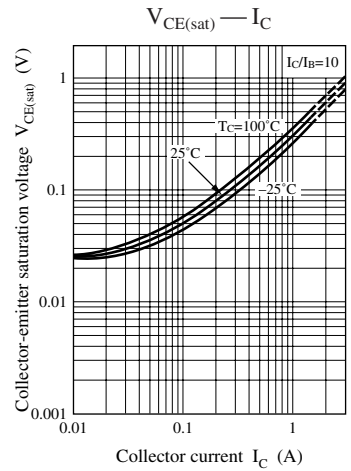
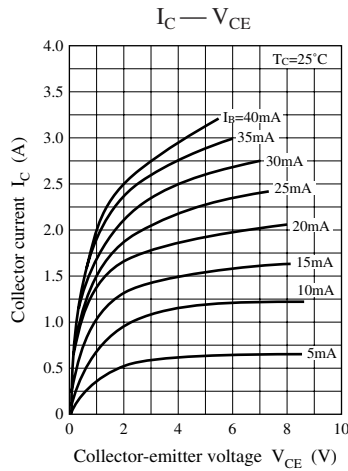
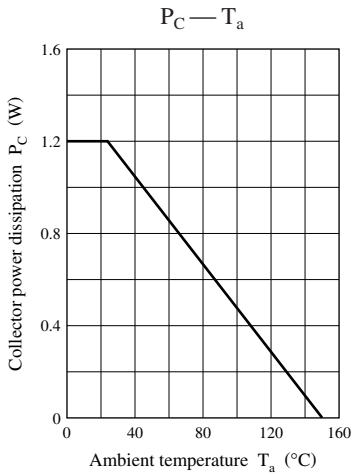
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|----------------------|---|-----|-----|-----|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_{\text{C}} = 1 \text{ mA}, I_{\text{E}} = 0$ | 50 | | | V |
| Collector-emitter voltage (Base open) | V_{CEO} | $I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$ | 40 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0$ | | | 1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{\text{CE}} = 10 \text{ V}, I_{\text{B}} = 0$ | | | 100 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{\text{EB}} = 5 \text{ V}, I_{\text{C}} = 0$ | | | 10 | μA |
| Forward current transfer ratio * | h_{FE} | $V_{\text{CE}} = 5 \text{ V}, I_{\text{C}} = 1 \text{ A}$ | 80 | | 220 | — |
| Collector-emitter saturation voltage | $V_{\text{CE(sat)}}$ | $I_{\text{C}} = 2 \text{ A}, I_{\text{B}} = 0.2 \text{ A}$ | | | 1 | V |
| Base-emitter saturation voltage | $V_{\text{BE(sat)}}$ | $I_{\text{C}} = 2 \text{ A}, I_{\text{B}} = 0.2 \text{ A}$ | | | 1.5 | V |
| Transition frequency | f_{T} | $V_{\text{CB}} = 5 \text{ V}, I_{\text{E}} = -0.5 \text{ A}, f = 200 \text{ MHz}$ | | 150 | | MHz |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$ | | 35 | | pF |

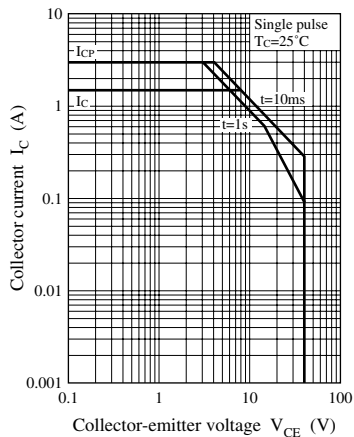
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

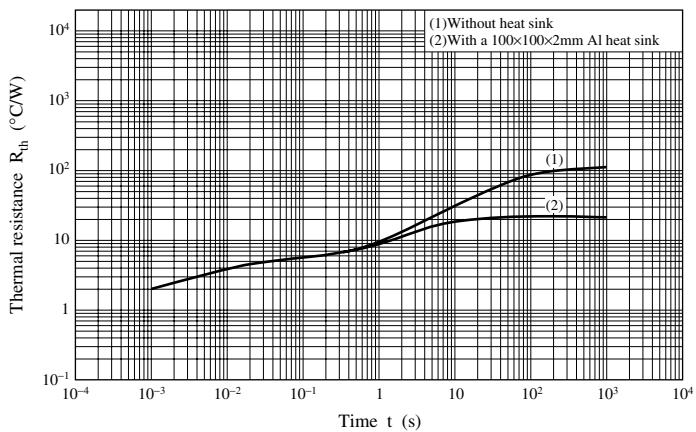
| Rank | Q | R |
|-----------------|-----------|------------|
| h_{FE} | 80 to 160 | 120 to 220 |



Safe operation area



R_{th} — t



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